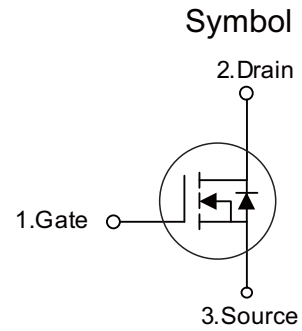


■ PRODUCT CHARACTERISTICS

VDSS	500V
$R_{DS(on)typ}(V_{GS}=10V)$	2.7Ω
Qg@type	18nC
ID	5A



■ APPLICATIONS

- High frequency switching mode power supply
- Electronic ballast
- LED power supply

■ FEATURES

- * Fast Switching Capability
- * Avalanche Energy Specified
- * Improved dv/dt Capability, High Ruggedness



■ ORDER INFORMATION

Order codes		Package	Packing
Halogen-Free	Halogen		
N/A	MOT5N50SBD	TO-252	2500 pieces /Reel

■ ABSOLUTE MAXIMUM RATINGS (T_c = 25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V _{DSS}	500	V
Gate-Source Voltage	V _{GSS}	±30	V
Drain Current	Continuous	I _D	5
	Pulse	I _{DM}	15
Avalanche Energy	Single Pulsed	E _{AS}	60
Power Dissipation	P _D	32.9	W
Junction Temperature	T _J	+150	°C
Storage Temperature	T _{STG}	-55~+150	°C

■ THERMAL DATA

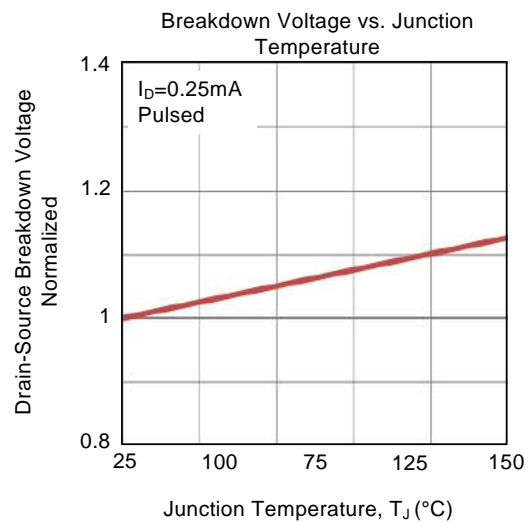
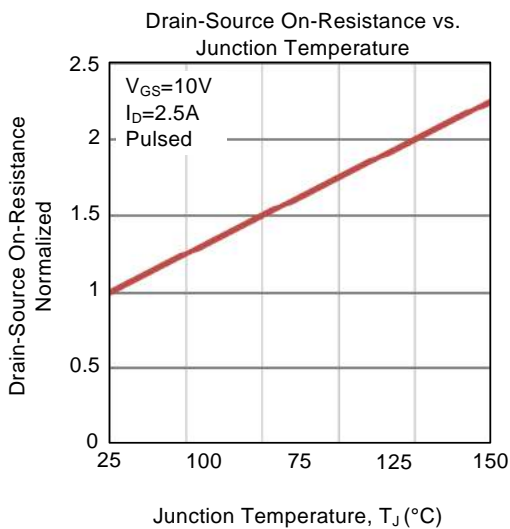
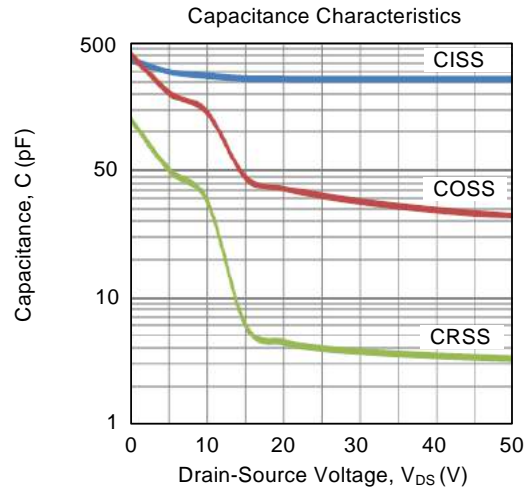
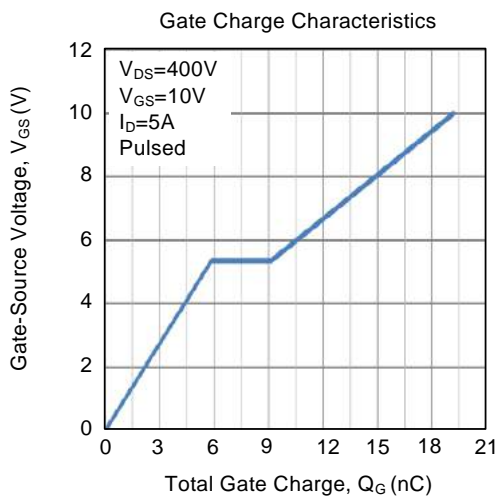
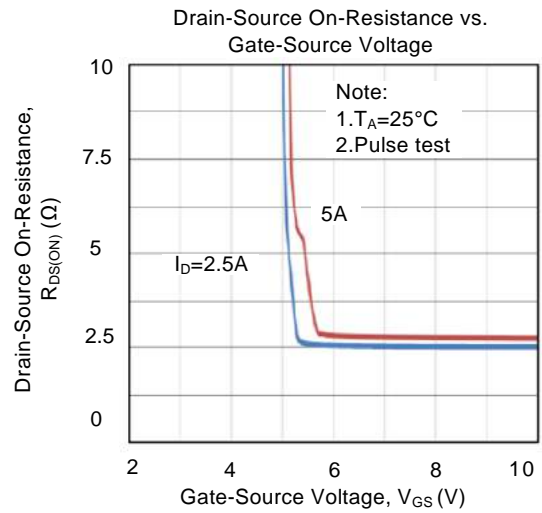
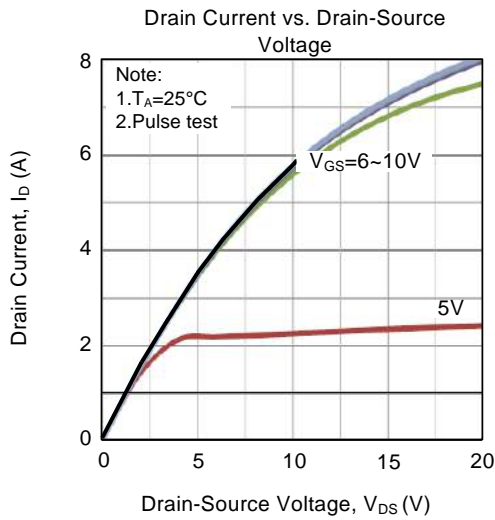
PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ _{JA}	62.5	°C/W
Junction to Case	θ _{JC}	6.25	°C/W

■ ELECTRICAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$, unless otherwise specified)

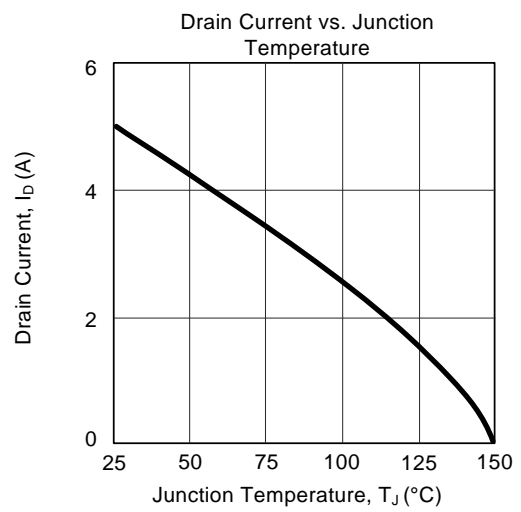
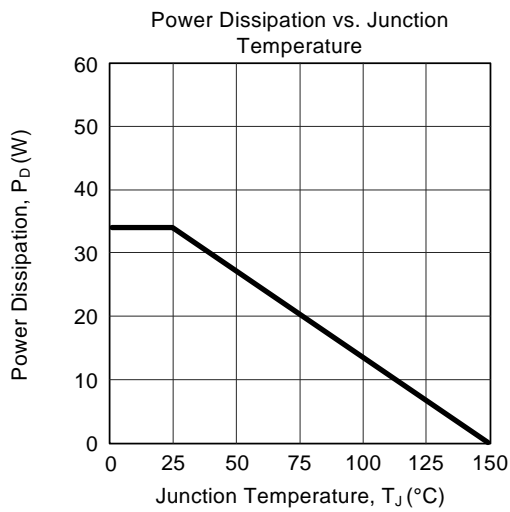
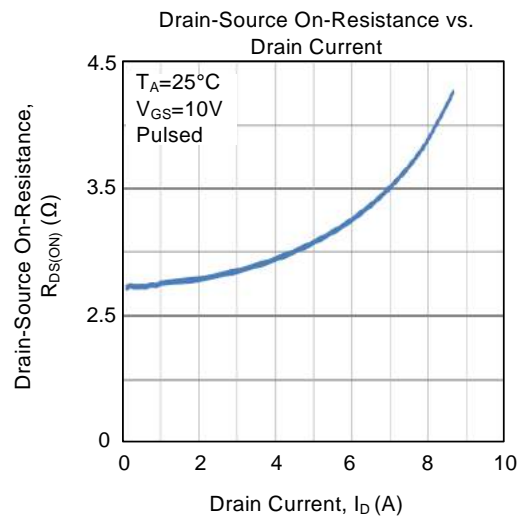
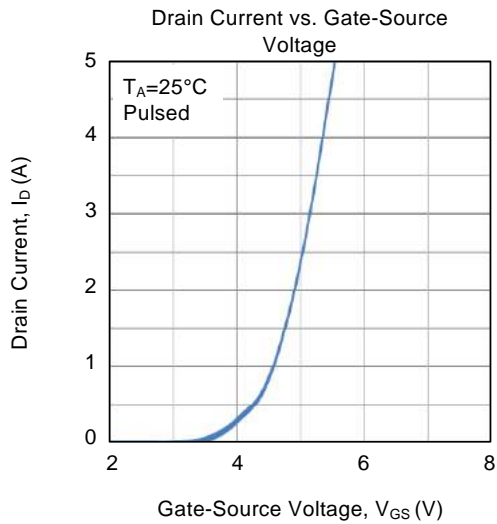
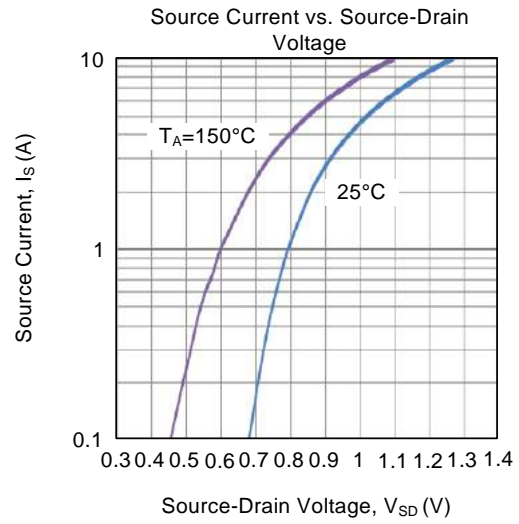
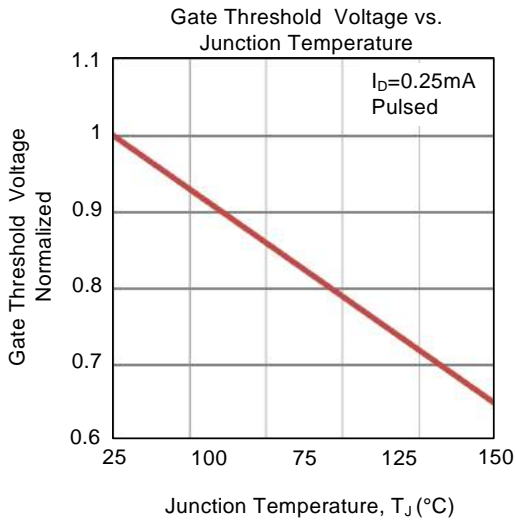
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	500	-	-	V
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	Reference to 25°C , $I_D=250\mu\text{A}$	-	0.5	-	$\text{V}/^\circ\text{C}$
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=500\text{V}$, $V_{GS}=0\text{V}$	-	-	1	μA
		$V_{DS}=400\text{V}$, $T_c=125^\circ\text{C}$	-	-	10	
Gate- Source Leakage Current	Forward	$V_{GS}=30\text{V}$, $V_{DS}=0\text{V}$	-	-	100	nA
	Reverse	$V_{GS}=-30\text{V}$, $V_{DS}=0\text{V}$	-	-	-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	2.0	-	4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=2.5\text{A}$	-	2.7	3.0	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}$, $V_{DS}=25\text{V}$, $f=1.0\text{MHz}$	-	320	-	pF
Output Capacitance	C_{OSS}		-	40	-	pF
Reverse Transfer Capacitance	C_{RSS}		-	8	-	pF
SWITCHING CHARACTERISTICS						
Total Gate Charge	Q_G	$V_{GS}=10\text{V}$, $V_{DS}=400\text{V}$, $I_D=5\text{A}$	-	18	-	nC
Gate to Source Charge	Q_{GS}		-	2.2	-	nC
Gate to Drain Charge	Q_{GD}		-	9.7	-	nC
Turn-ON Delay Time	$t_{D(ON)}$	$V_{DD}=250\text{V}$, $I_D=5\text{A}$, $R_G=25\Omega$	-	12	-	ns
Rise Time	t_R		-	46	-	ns
Turn-OFF Delay Time	$t_{D(OFF)}$		-	50	-	ns
Fall-Time	t_F		-	48	-	ns
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I_S		-	-	5	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}		-	-	15	A
Drain-Source Diode Forward Voltage	V_{SD}	$I_S=5\text{A}$, $V_{GS}=0\text{V}$	-	-	1.4	V
Reverse Recovery Time	t_{rr}	$I_S=5\text{A}$, $V_{GS}=0\text{V}$,	-	97	-	ns
Reverse Recovery Charge	Q_{RR}	$di_F/dt=100\text{A}/\mu\text{s}$ (Note 1)	-	0.25	-	μC

 Note: 1. Pulse Test: Pulse width 300 μs , Duty cycle 2%

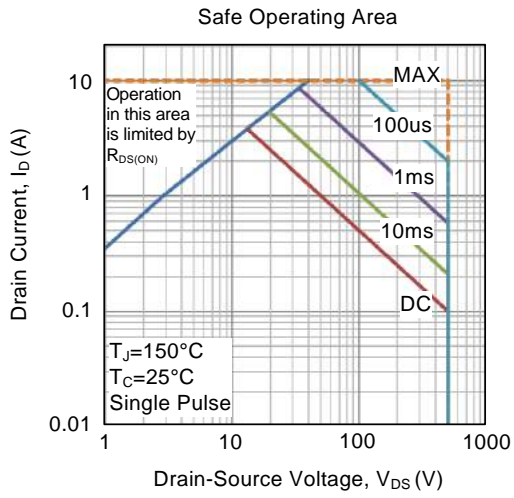
■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS(Cont.)



■ TYPICAL CHARACTERISTICS(Cont.)



■ TO-252 PACKAGE OUTLINE DIMENSIONS

